

GaN Broad Band UV Photodiode

UV1.0TF-3



Description

UV1.0TF-3 is a broad band GaN based UV photodiode. It is optimized for Ultra-violet range 210~370 nm, It can be easily selected with integral filters. It is packaged in electrically isolated and hermetically sealed TO46 metal can with quartz window.

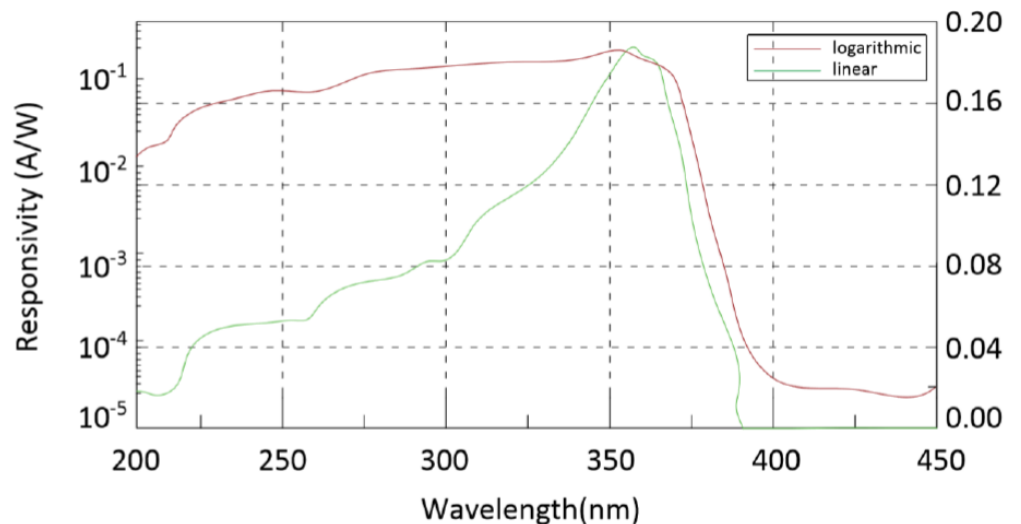
Features

*High reliability in demanding environments

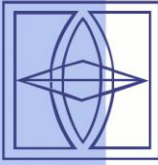
Applications

- * Sunlight exposure meter
- * Water purification facilities
- * UV power meter

Spectral Response



OEC



Opto-Electronic
Components

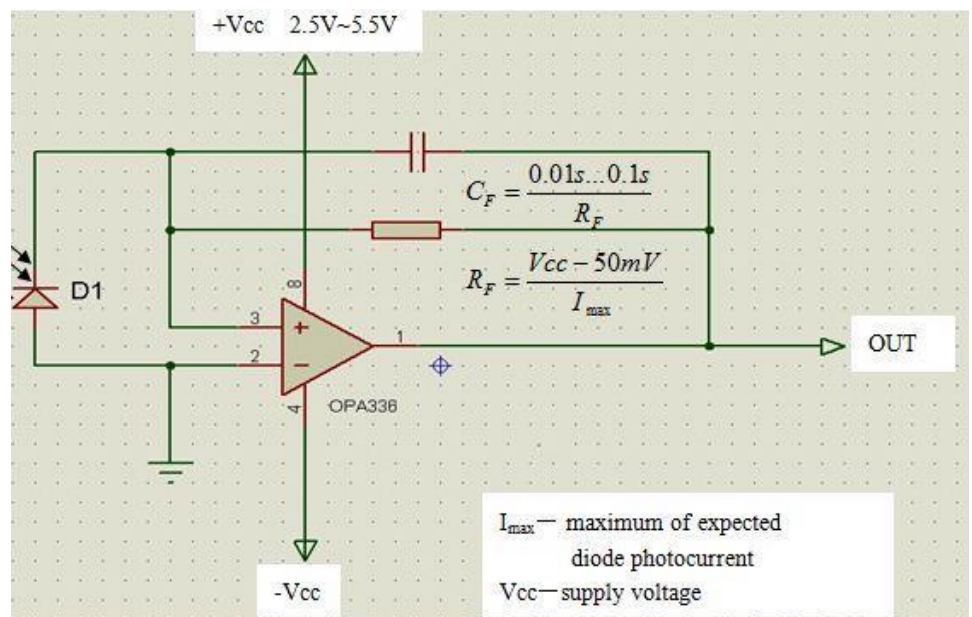


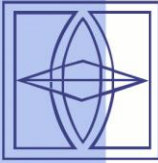
YOUR PARTNER

Electro-Optical Characteristics

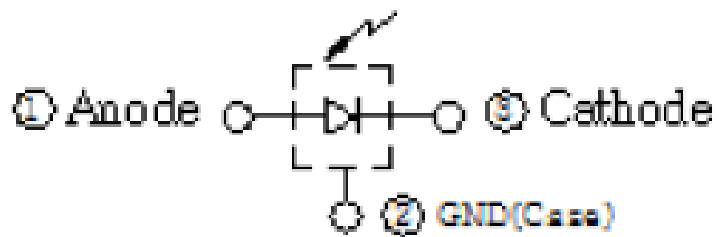
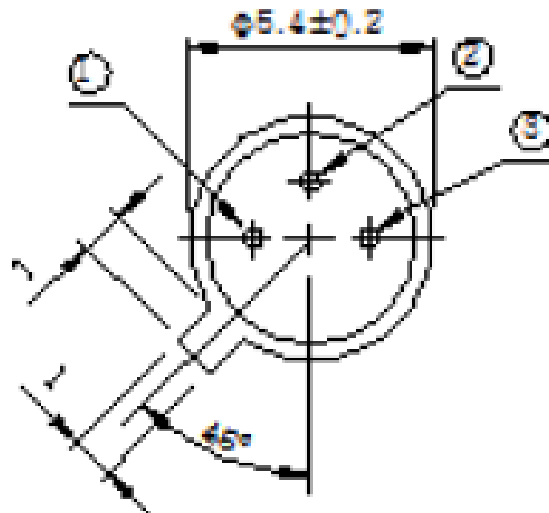
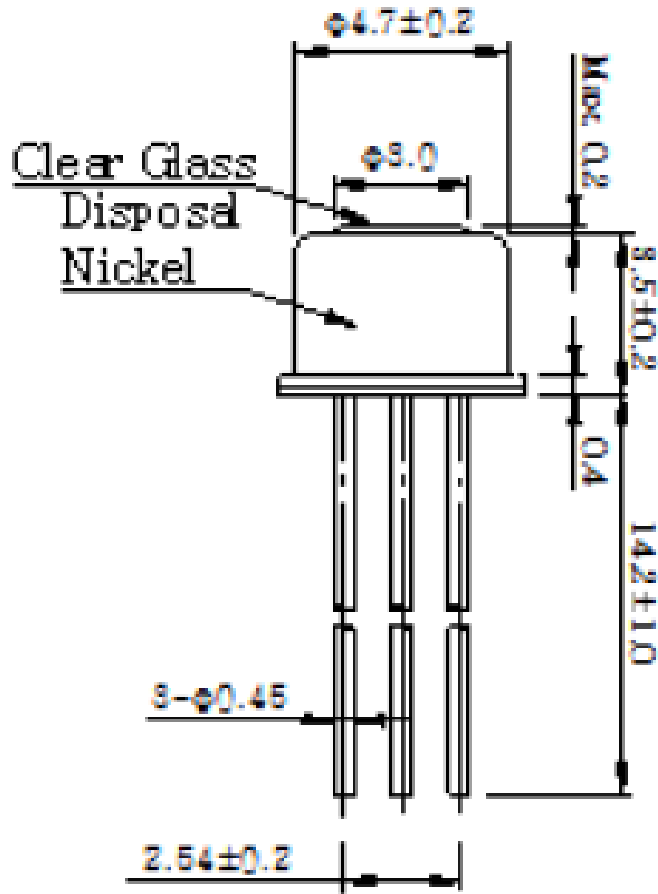
Parameter	Symbol	Min.	Typ.	Max.	Unit
Operation temperature range	Topt	-25		+85	°C
Storage temperature range	Tsto	-40		+85	°C
Soldering temperature (3s)	Tsol		260		°C
Reverse voltage	Vr		-10		V
Chip size (active area)	A		1.0		mm ²
Dark current (Vr=-5V)	Id			1	nA
Temperature coefficient	Tc		-0.02		%/°C
Capacitance (Vr=0V, f=1MHz)	Cj		40		pF
Wavelength of peak responsivity	λ_p		355		nm
Peak responsivity (@355nm)	Rmax		0.15		A/W
Spectral response range (R=0.1*Rmax)	S _R	210		375	nm
UV-Visible rejection ratio(Rmax/R400nm)	-	10 ⁴			-

Typical Application Circuit





Package Drawing



All Dimensions in „mm“